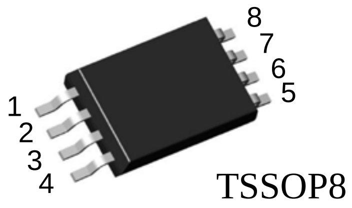
Dual N-Channel High Density Trench MOSFET (20V, 7A)

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(on)}$ (m-ohm) Max
20V	7A	$R_{DS(on)} < 20$ @ $V_{GS} = 4.5V$, I_D=7A
		$R_{DS(on)} < 21$ @ $V_{GS} = 4.0V$, I_D=7A
		$R_{DS(on)} < 28$ @ $V_{GS} = 2.5V$, I_D=5.5A

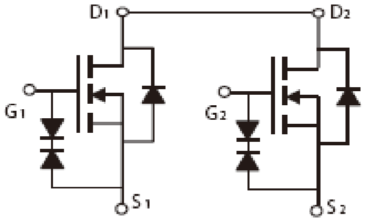
Features

- Super high dense cell trench design for low $R_{DS(on)}$
- Rugged and reliable
- Surface Mount package
- Battery Switch ESD Protected 2KV
- Ordering information：KF8810 （Lead（Pb）-free）

  KF8810 -G（Lead（Pb）-free and halogen-free）



TSSOP8



Pin 1/ 8: Drain
Pin 2/ 3: Source 1
Pin 4: Gate 1
Pin 5: Gate 2
Pin 6/ 7: Source 2

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±10	V
I_D	Drain Current (Continuous)	7	A
I_{DM}	Drain Current (Pulsed) [a]	30	A
P_D	Total Power Dissipation @T_A=25°C	1.5	W
I_S	Maximum Diode Forward Current	1.5	A
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (PCB mounted)[b]	83	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperature
b: 1-in^2 2oz Cu PCB board